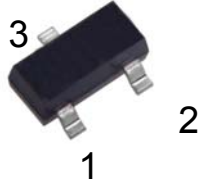
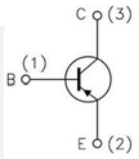




## SOT-23 Plastic-Encapsulate Transistors

<p><b>MMBT5401</b></p> <p><b>Features:</b></p> <ul style="list-style-type: none"> <li><input type="checkbox"/> PNP Transistor</li> <li><input type="checkbox"/> Complementary to MMBT5551</li> <li><input type="checkbox"/> Ideal for Medium Power Amplification and Switching</li> </ul> <p><b>Marking:2L</b></p>	<p>SOT-23</p>   <p>1.Base (B) 2. Emitter (E) 3. Collector (C)</p>
--	---

**Absolute Maximum Ratings** (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-160	V
Collector-Emitter Voltage	$V_{CEO}$	-150	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	0.6	A
Collector Power Dissipation	PD	0.3	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	416	°C/W
Junction Temperature(MAX.)	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C

**Electrical Characteristics** (Ta=25°C unless otherwise noted)

Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-160	-	-	V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-150	-	-	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5	-	-	V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -120V, I_E = 0$	-	-	-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4V, I_C = 0$	-	-	-0.1	$\mu A$
DC current gain	$h_{FE(1)}^*$	$V_{CE} = -5V, I_C = -1mA$	80	-	-	-
	$h_{FE(2)}^*$	$V_{CE} = -5V, I_C = -10mA$	100	-	300	-
	$h_{FE(3)}^*$	$V_{CE} = -5V, I_C = -50mA$	50	-	-	-
Collector-emitter saturation voltage	$V_{CE(sat)1}^*$	$I_C = -10mA, I_B = -1mA$	-	-	-0.2	V
	$V_{CE(sat)2}^*$	$I_C = -50mA, I_B = -5mA$	-	-	-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)1}^*$	$I_C = -10mA, I_B = -1mA$	-	-	-1	V
	$V_{BE(sat)2}^*$	$I_C = -50mA, I_B = -5mA$	-	-	-1	V
Transition frequency	FT	$V_{CE} = -5V, I_C = -10mA, f = 30MHz$	100	-	-	MHz

**CLASSIFICATION OF hFE (2)**

RANK	L	H
RANGE	100-200	200-300

\*Pulse test: pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2.0\%$ .



# SOT-23 Plastic-Encapsulate Transistors

## Typical Characteristics

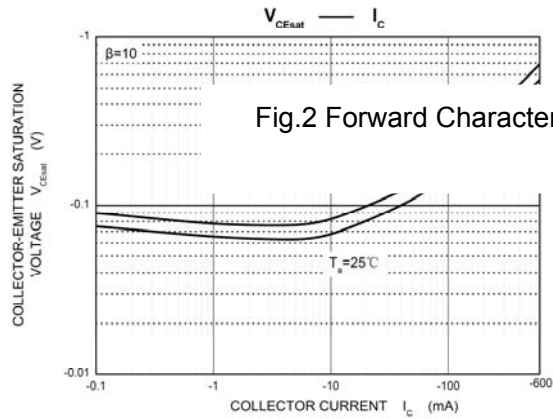
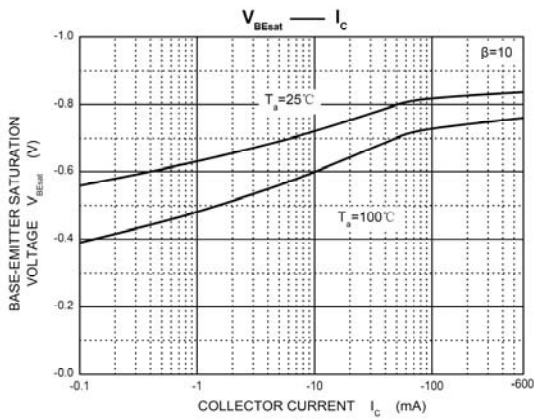
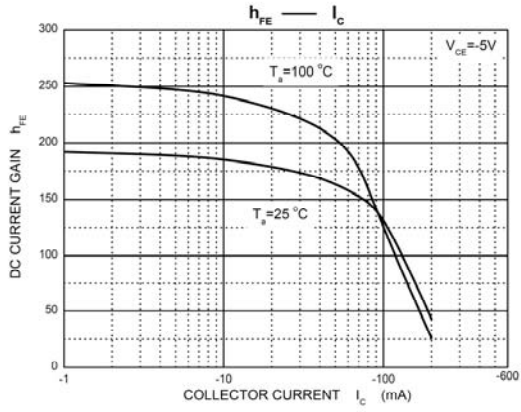
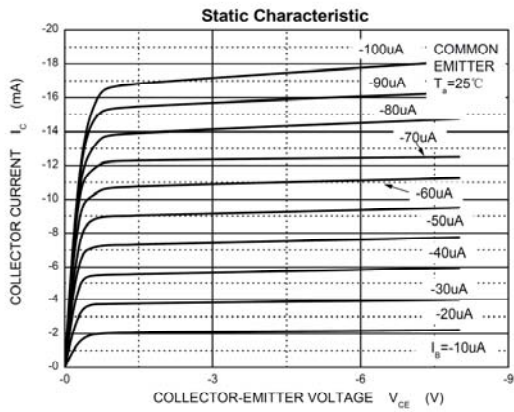
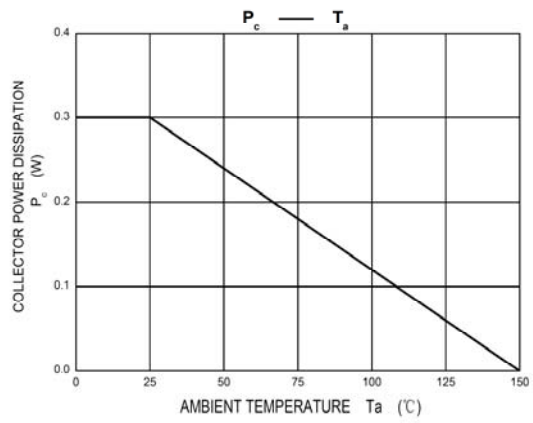
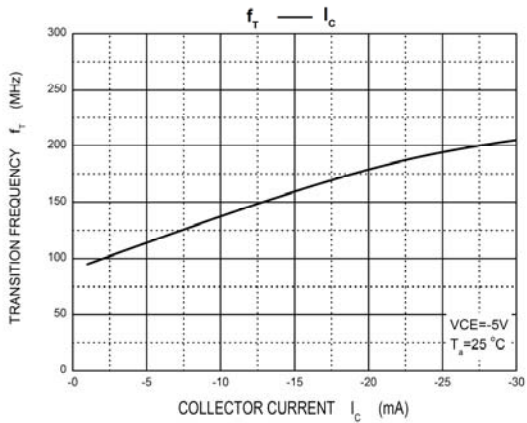
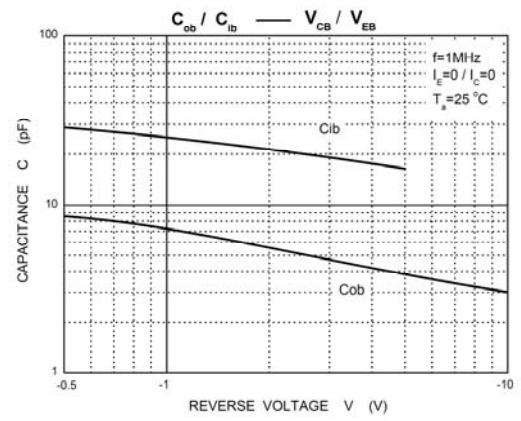
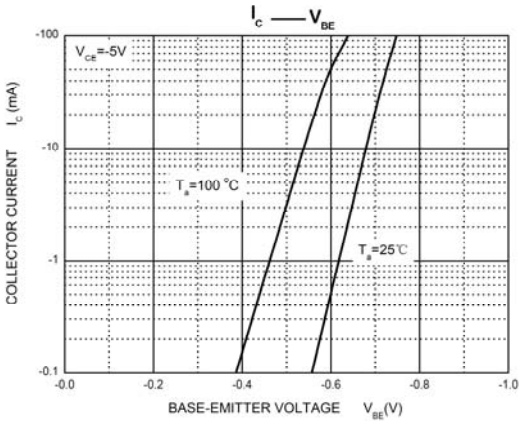


Fig.2 Forward Characteristics

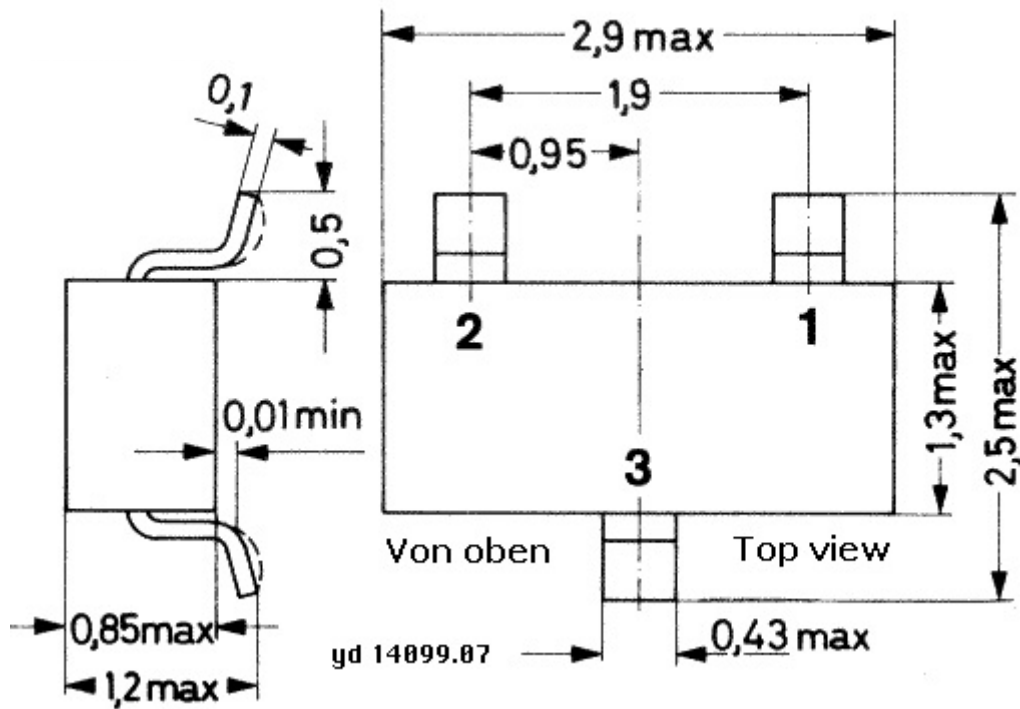


## SOT-23 Plastic-Encapsulate Transistors

### Package Dimension

SOT-23

Unit: mm



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